Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3614	257/758.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 03:51
S3	221	257/758.ccls. and @ad<"20031030" and dummy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 03:52
S2	3147	257/758.ccls. and @ad<"20031030"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 03:52
S5	0	257/725.ccls. and @ad<"20031030" and dummy and (CMP or polish$4) and (cvd or vapor adj deposition)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 04:11
S6	2	257/725.ccls. and @ad<"20031030" and dummy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 04:12
S4	88	257/758.ccls. and @ad<"20031030" and dummy and (CMP or polish$4) and (cvd or vapor adj deposition)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 04:12
S7	46	438/926.ccls. and @ad<"20031030" and dummy and (CMP or polish$4) and (cvd or vapor adj deposition)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 04:16
L2	46	438/926.ccls. and @ad<"20031030" and dummy and (CMP or polish$4) and (cvd or vapor adj deposition)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 10:40

L1	116	438/926.ccls. and @ad<"20031030" and dummy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 10:40
L3	70	438/926.ccls. and @ad<"20031030" and dummy not L2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 10:48
L8	884	semiconductor and (wiring or conductor or electrode) and @ad<"20031030" and (dummy with (pattern$3 or structure)) and (CMP or polish$4) and (cvd or vapor adj deposition)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 10:51
L7	4347	semiconductor and (wiring or conductor or electrode) and @ad<"20031030" and (dummy with (pattern$3 or structure))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 10:51